SPP04N50C3XKSA1 Datasheet

DiGi Electronics Part Number	SPP04N50C3XKSA1-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	SPP04N50C3XKSA1
Description	LOW POWER_LEGACY
Detailed Description	N-Channel 560 V 4.5A (Tc) 50W (Tc) Through Hole PG-TO220-3-1

https://www.DiGi-Electronics.com

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RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
SPP04N50C3XKSA1	Infineon Technologies
Series:	Product Status:
CoolMOS™	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
560 V	4.5A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	950mOhm @ 2.8A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3.9V @ 200µA	22 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	470 pF @ 25 V
FET Feature:	Power Dissipation (Max):
-	50W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
PG-TO220-3-1	TO-220-3
Base Product Number:	
SPP04N	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

SPP04N50C3
SPA04N50C3

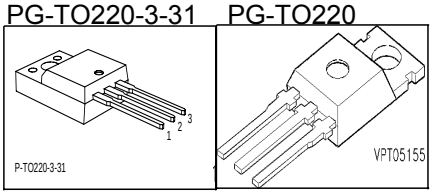
Cool MOS™ Power Transistor

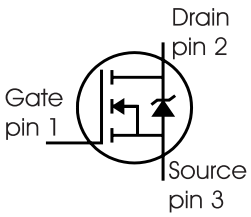
V_{DS} @ T_{jmax}	560	V
$R_{DS(on)}$	0.95	Ω
I_D	4.5	A

Feature

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme d*v*/d*t* rated
- Ultra low effective capacitances
- Improved transconductance
- PG-TO-220-3-31: Fully isolated package (2500 VAC; 1 minute)
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC[0)] for target applications

PG-TO220-3-31 PG-TO220





Type	Package	Ordering Code	Marking
SPP04N50C3	PG-TO220	Q67040-S4575	04N50C3
SPA04N50C3	PG-TO220-3-31	SP000216298	04N50C3

Maximum Ratings

Parameter	Symbol	Value		Unit
		SP	SPA	
Continuous drain current	I_D			A
T_C = 25 °C		4.5	4.5[1)]	
T_C = 100 °C		2.8	2.8[1)]	
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\ puls}$	13.5	13.5	A
Avalanche energy, single pulse	E_{AS}	130	130	mJ
I_D=3.4A, V_{DD}=50V				
Avalanche energy, repetitive t_{AR} limited by T_{jmax}[2)]	E_{AR}	0.4	0.4	
I_D=4.5A, V_{DD}=50V				
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	4.5	4.5	A
Gate source voltage	V_{GS}	±20	±20	V
Gate source voltage AC (f >1Hz)	V_{GS}	±30	±30	
Power dissipation, T_C = 25°C	P_{tot}	50	31	W
Operating and storage temperature	T_j , T_{stg}	-55...+150		°C
Reverse diode dv/dt [7)]	dv/dt	15		V/ns

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope V_{DS} = 400 V, I_D = 4.5 A, T_j = 125 °C	d*v*/d*t*	50	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	2.5	K/W
Thermal resistance, junction - case, FullPAK	R_{thJC_FP}	-	-	4	
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Thermal resistance, junction - ambient, FullPAK	R_{thJA_FP}	-	-	80	
SMD version, device on PCB: @ min. footprint @ 6 cm^2 cooling area [3]	R_{thJA}	 - -	 - 35	 62 -	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s [4]	T_{sold}	-	-	260	°C

Electrical Characteristics, at T_j=25°C unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=0.25mA	500	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	V_{GS}=0V, I_D=4.5A	-	600	-	
Gate threshold voltage	$V_{GS(th)}$	I_D=200µA, V_{GS}=V_{DS}	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	V_{DS}=500V, V_{GS}=0V, T_j=25°C T_j=150°C	 - -	 0.1 -	 1 100	µA
Gate-source leakage current	I_{GSS}	V_{GS}=20V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=2.8A T_j=25°C T_j=150°C	 - -	 0.85 2.3	 0.95 -	Ω
Gate input resistance	R_G	*f*=1MHz, open drain	-	1.4	-	

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	$V_{DS}\geq 2*I_D*R_{DS(on)max}$, I_D=2.8A	-	4.4	-	S
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	470	-	pF
Output capacitance	C_{oss}		-	160	-	
Reverse transfer capacitance	C_{rss}		-	15	-	
Effective output capacitance,[5] energy related	$C_{o(er)}$	V_{GS}=0V, V_{DS}=0V to 400V	-	27	-	
Effective output capacitance,[6] time related	$C_{o(tr)}$		-	44	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=350V, V_{GS}=0/10V, I_D=4.5A, R_G=18Ω	-	10	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	70	-	
Fall time	t_f		-	10	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	V_{DD}=400V, I_D=4.5A	-	2.2	-	nC
Gate to drain charge	Q_{gd}		-	10	-	
Gate charge total	Q_g	V_{DD}=400V, I_D=4.5A, V_{GS}=0 to 10V	-	22	-	
Gate plateau voltage	$V_{(plateau)}$	V_{DD}=400V, I_D=4.5A	-	5	-	V

[0]J-STD20 and JESD22

[1]Limited only by maximum temperature

[2]Repetitve avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR}*f$.

[3]Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

[4]Soldering temperature for TO-263: 220°C, reflow

[5]$C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

[6]$C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

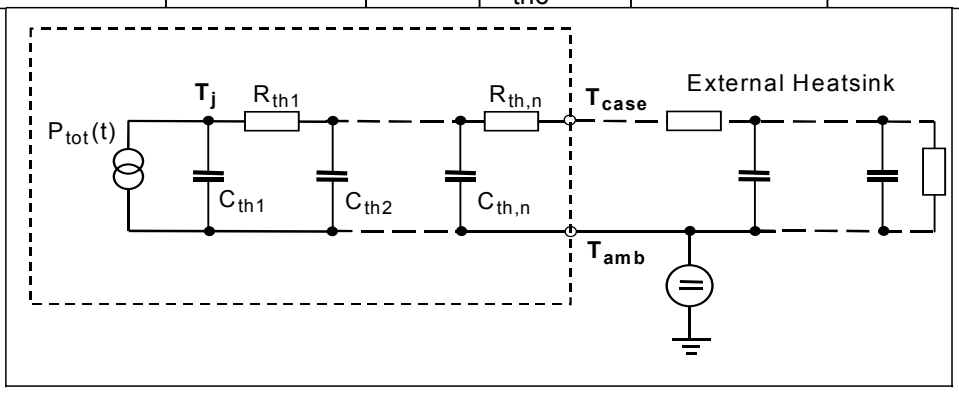
[7]I_{SD}<=I_D, di/dt<=400A/us, V_{DClink}=400V, V_{peak}<$V_{BR, DSS}$, T_j<$T_{j,max}$.
Identical low-side and high-side switch.

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	T_C=25°C	-	-	4.5	A
Inverse diode direct current, pulsed	I_{SM}		-	-	13.5	
Inverse diode forward voltage	V_{SD}	V_{GS}=0V, I_F=I_S	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=400V, I_F=I_S ,	-	280	-	ns
Reverse recovery charge	Q_{rr}	di_F/dt=100A/µs	-	2.3	-	µC
Peak reverse recovery current	I_{rrm}		-	16	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt	T_j=25°C	-	860	-	A/µs

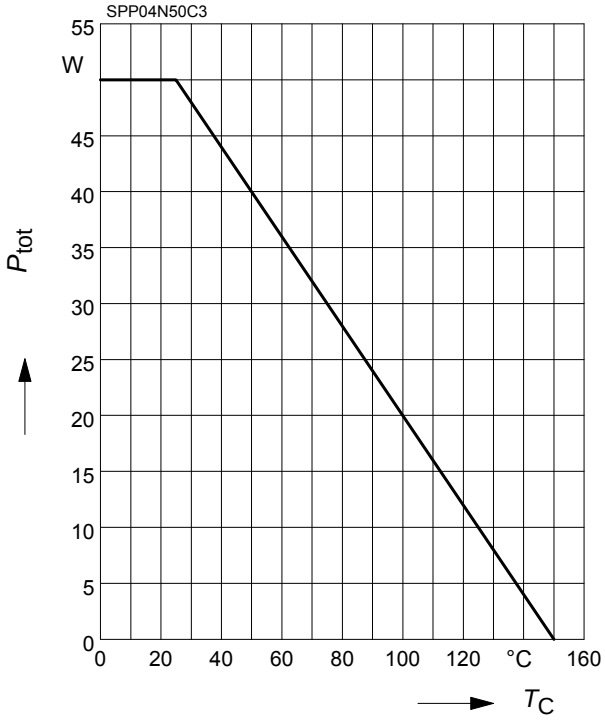
Typical Transient Thermal Characteristics

Symbol	Value		Unit	Symbol	Value		Unit
	SPP_B	SPA			SPP_B	SPA	
R_{th1}	0.039	0.039	K/W	C_{th1}	0.00007347	0.00007347	Ws/K
R_{th2}	0.074	0.074		C_{th2}	0.0002831	0.0002831	
R_{th3}	0.132	0.132		C_{th3}	0.0004062	0.0004062	
R_{th4}	0.555	0.272		C_{th4}	0.001215	0.001215	
R_{th5}	0.529	0.559		C_{th5}	0.00276	0.005633	
R_{th6}	0.169	2.523		C_{th6}	0.029	0.412	



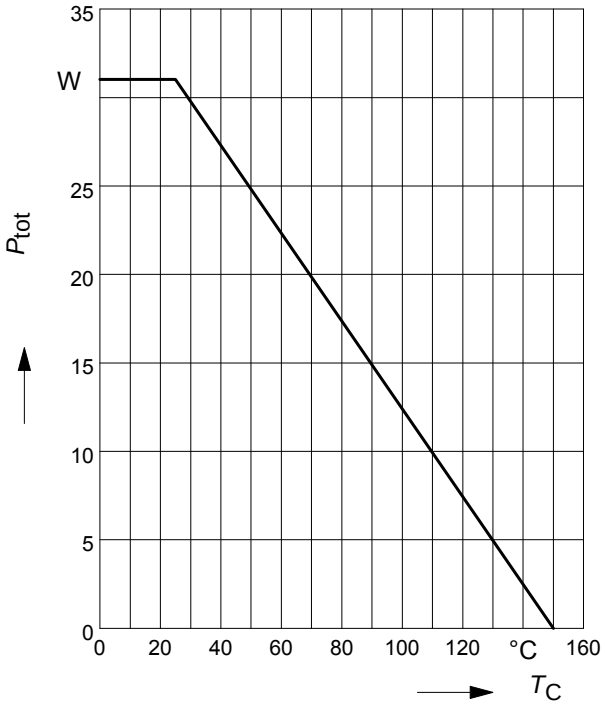
1 Power dissipation

$P_{tot} = f(T_C)$



2 Power dissipation FullPAK

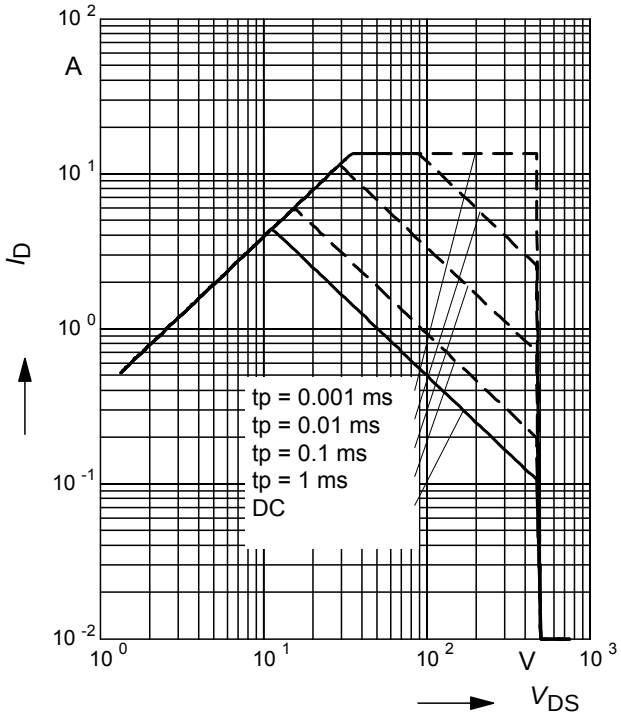
$P_{tot} = f(T_C)$



3 Safe operating area

$I_D = f(V_{DS})$

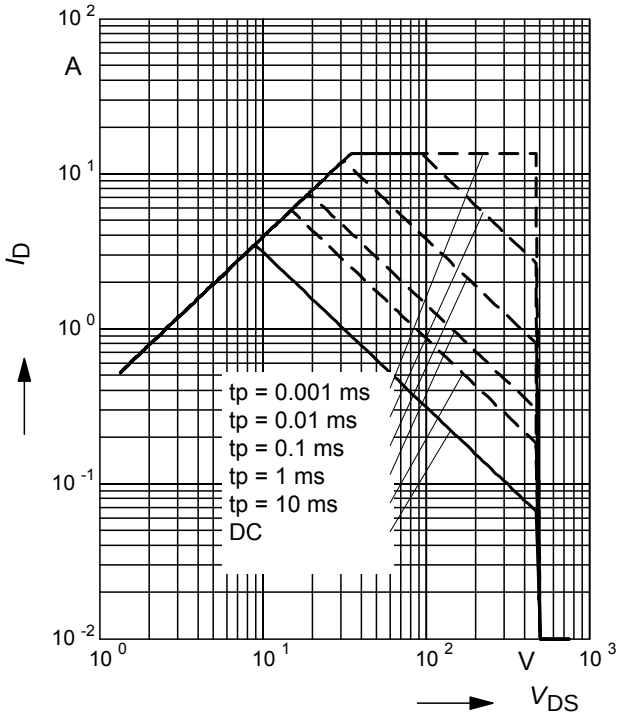
parameter : $D = 0$, T_C=25°C



4 Safe operating area FullPAK

$I_D = f(V_{DS})$

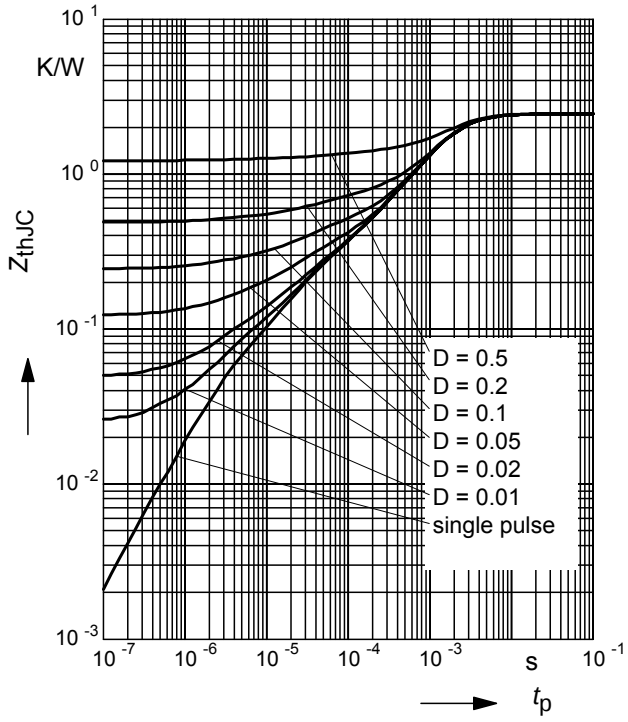
parameter: $D = 0$, $T_C = 25°C$



5 Transient thermal impedance

$Z_{thJC} = f(t_p)$

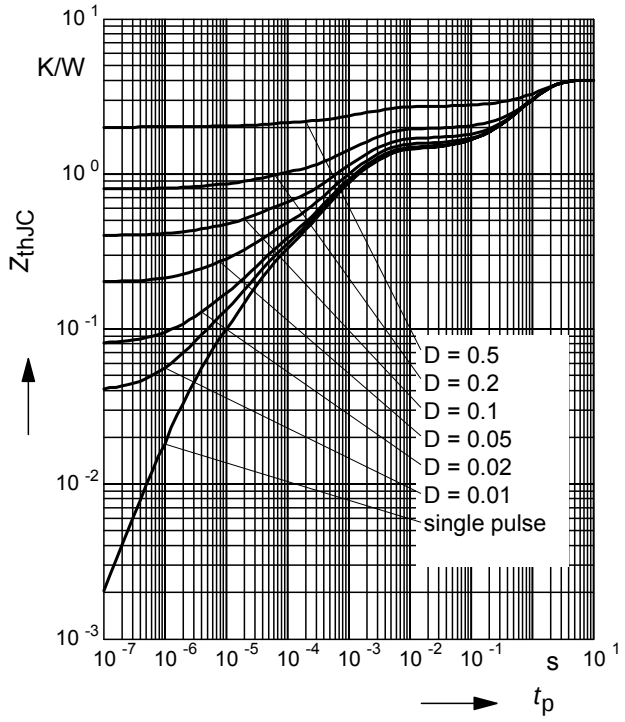
parameter: $D = t_p/T$



6 Transient thermal impedance FullPAK

$Z_{thJC} = f(t_p)$

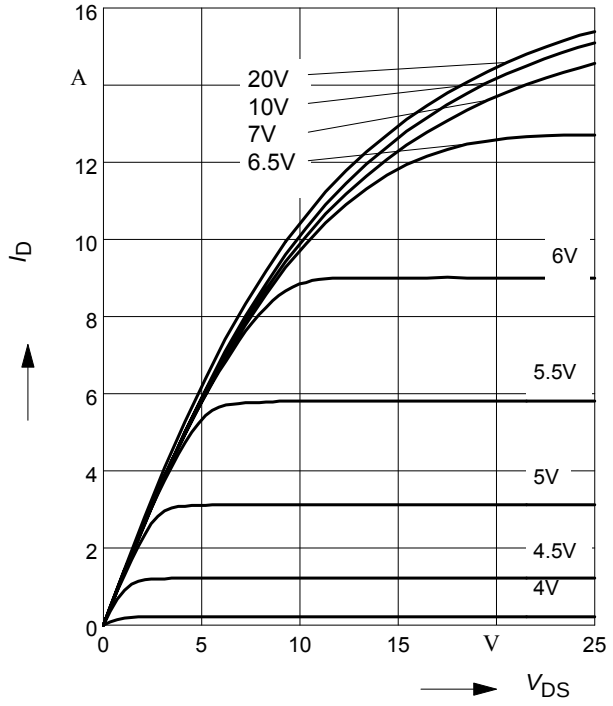
parameter: $D = t_p/t$



7 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=25°C

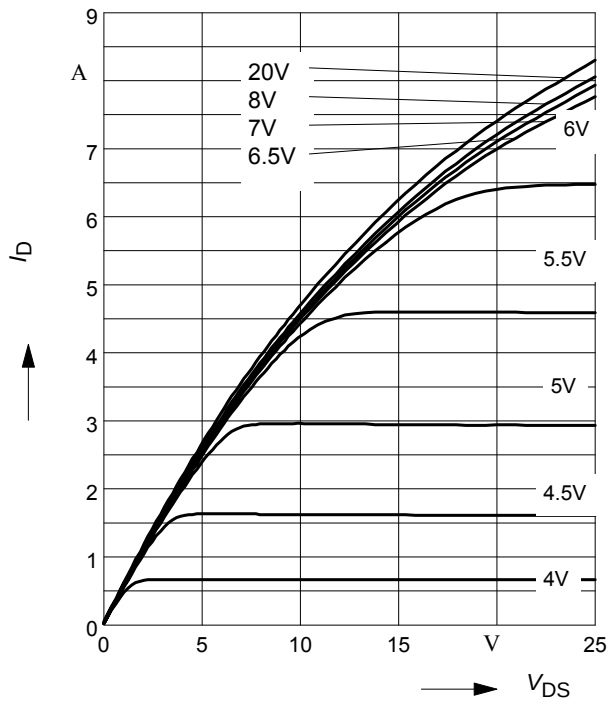
parameter: t_p = 10 µs, V_{GS}



8 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=150°C

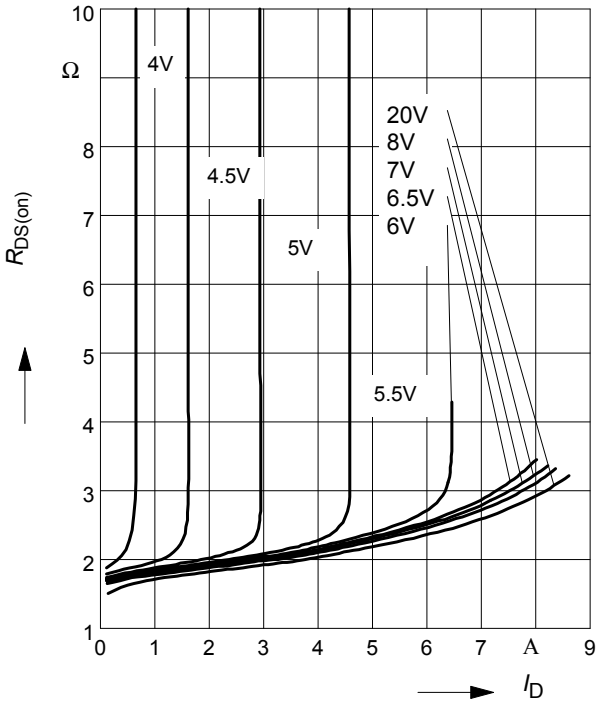
parameter: t_p = 10 µs, V_{GS}



9 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$

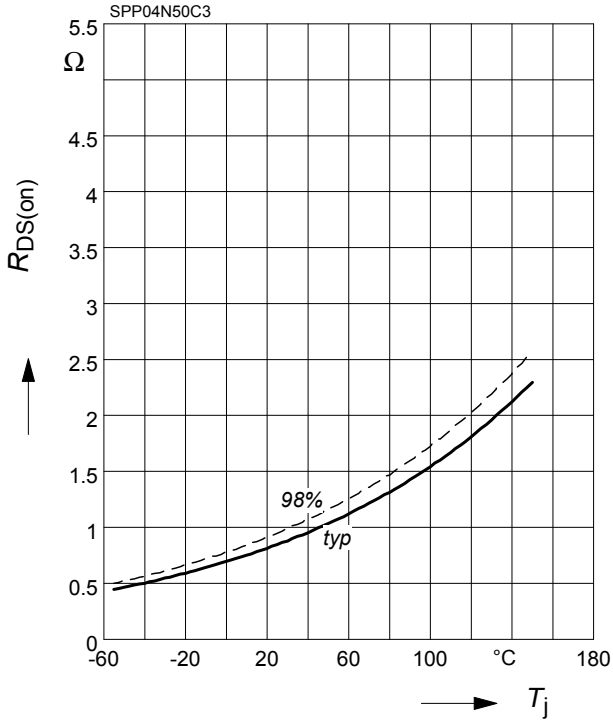
parameter: T_j=150°C, V_{GS}



10 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

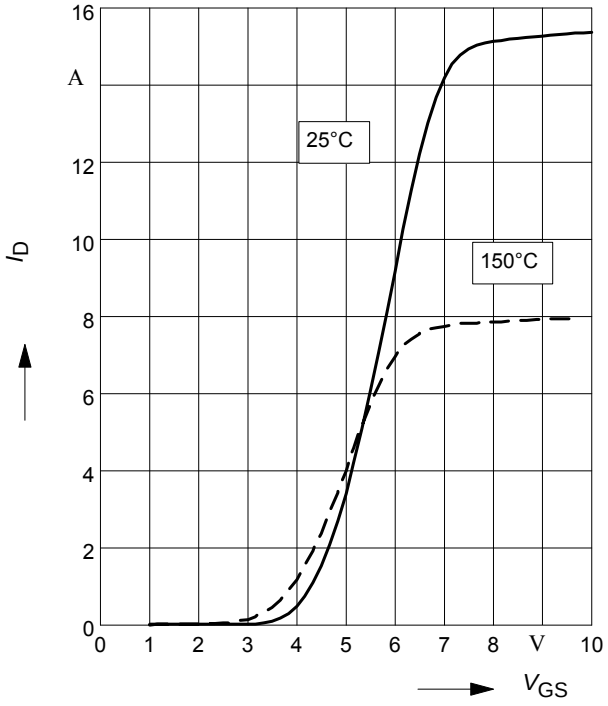
parameter : I_D = 2.8 A, V_{GS} = 10 V



11 Typ. transfer characteristics

$I_D = f(V_{GS})$; $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

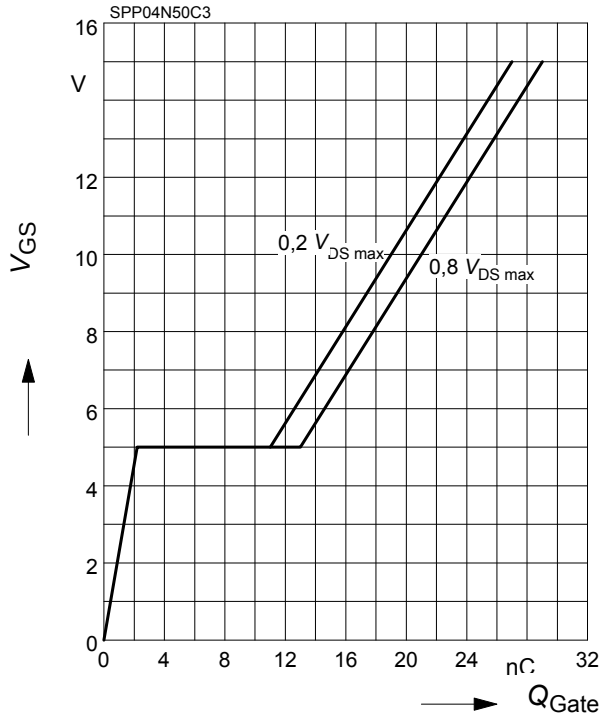
parameter: t_p = 10 µs



12 Typ. gate charge

$V_{GS} = f(Q_{Gate})$

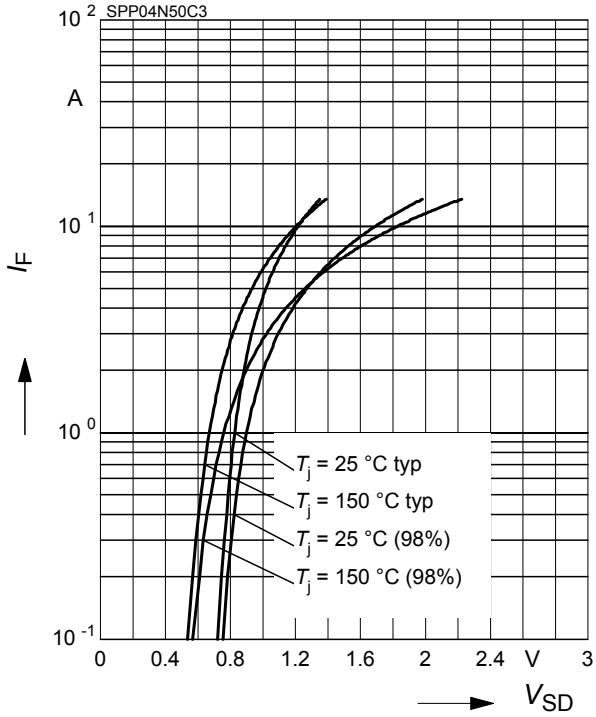
parameter: I_D = 4.5 A pulsed



13 Forward characteristics of body diode

$I_F = f(V_{SD})$

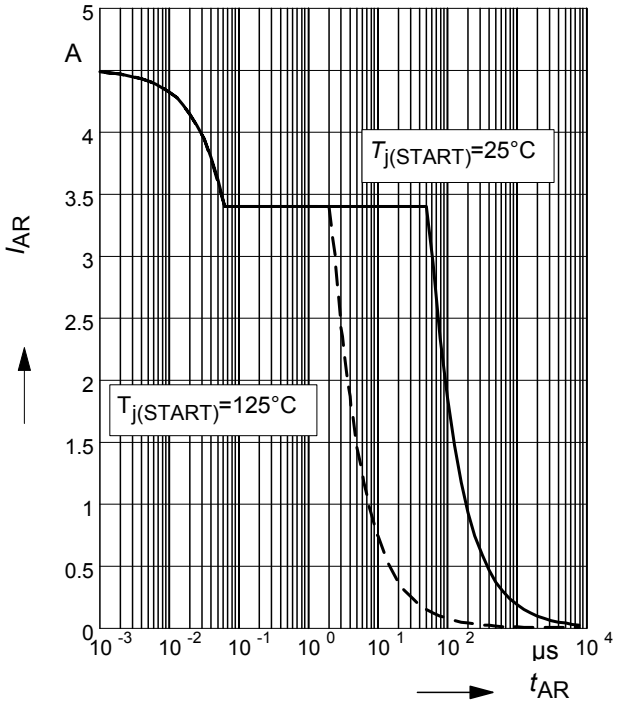
parameter: T_j , tp = 10 µs



14 Avalanche SOA

$I_{AR} = f(t_{AR})$

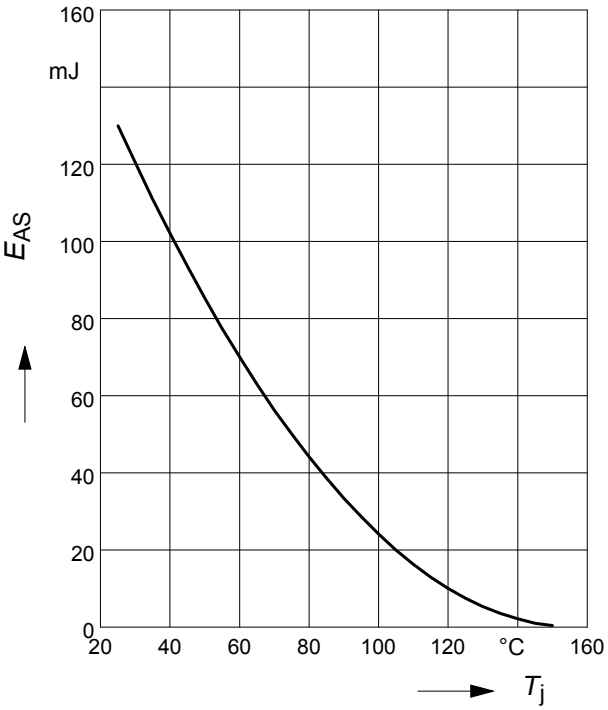
par.: $T_j \leq 150$ °C



15 Avalanche energy

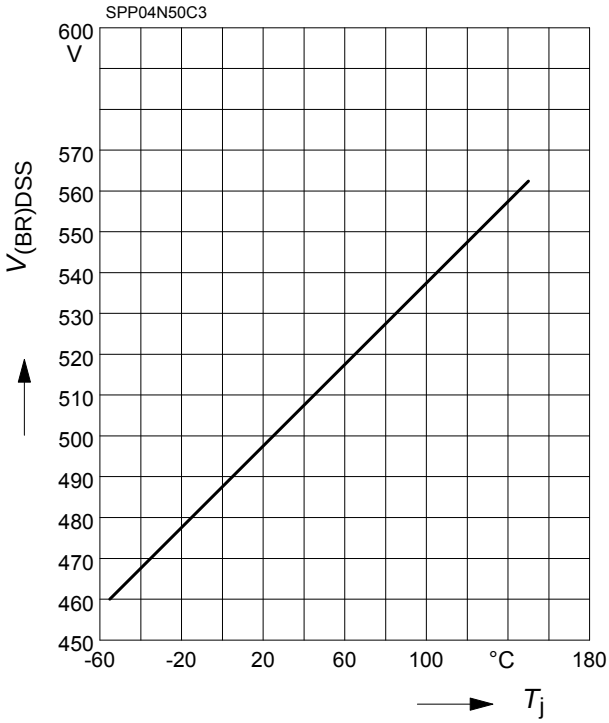
$E_{AS} = f(T_j)$

par.: I_D = 3.4 A, V_{DD} = 50 V



16 Drain-source breakdown voltage

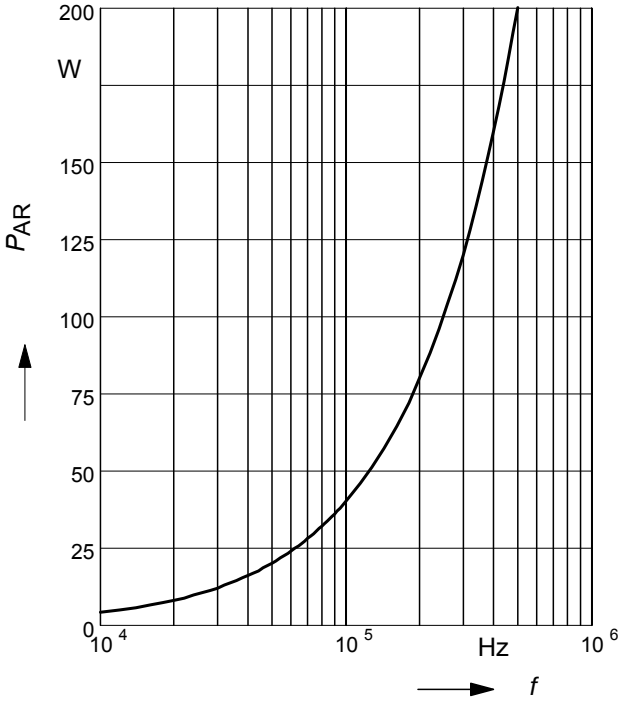
$V_{(BR)DSS} = f(T_j)$



17 Avalanche power losses

$P_{AR} = f(f)$

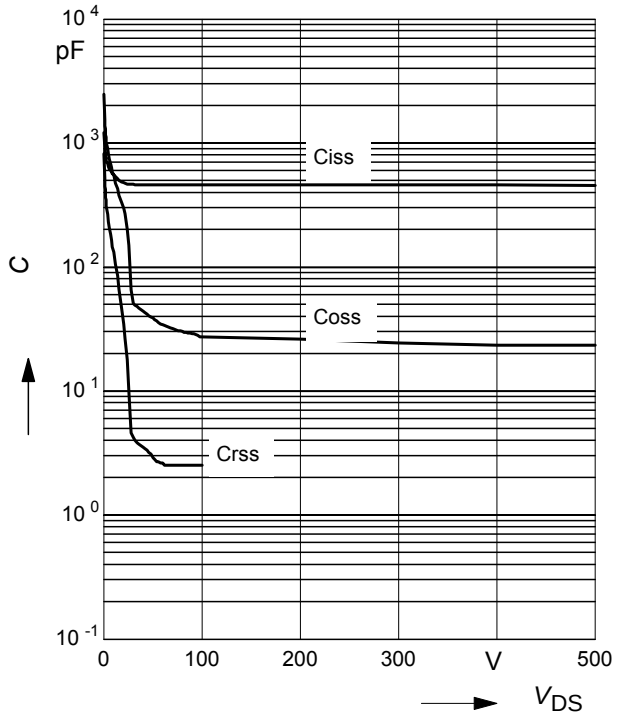
parameter: E_{AR}=0.4mJ



18 Typ. capacitances

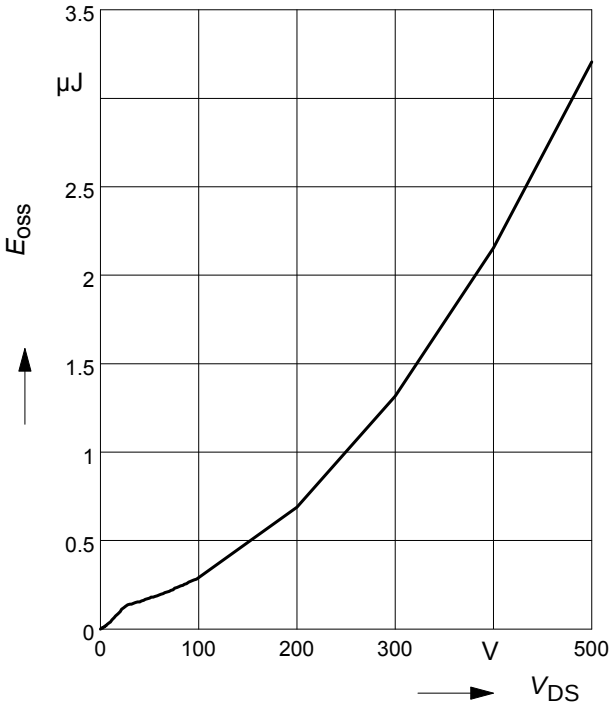
$C = f(V_{DS})$

parameter: V_{GS}=0V, f=1 MHz

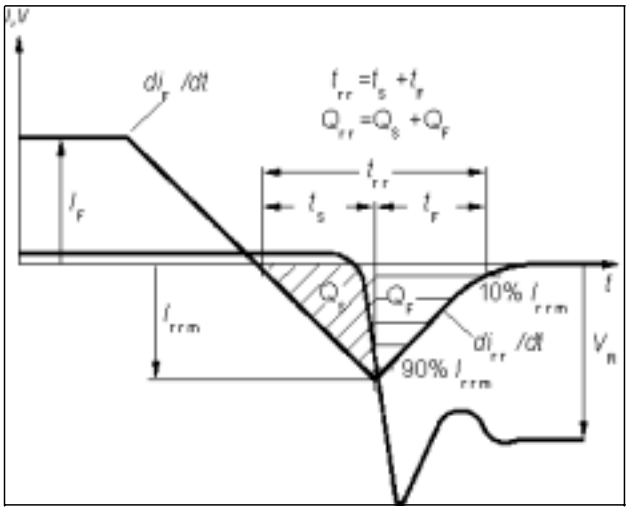


19 Typ. C_{oss} stored energy

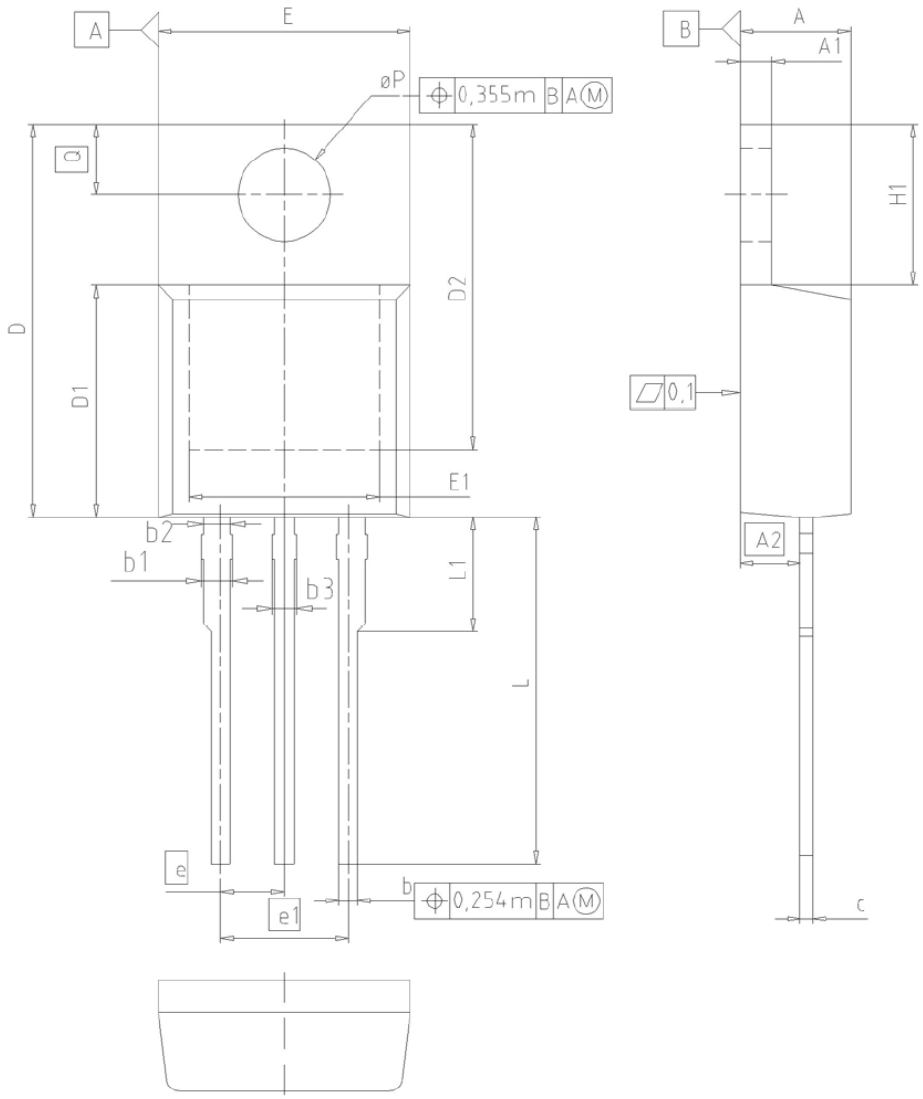
$E_{oss}=f(V_{DS})$



Definition of diodes switching characteristics



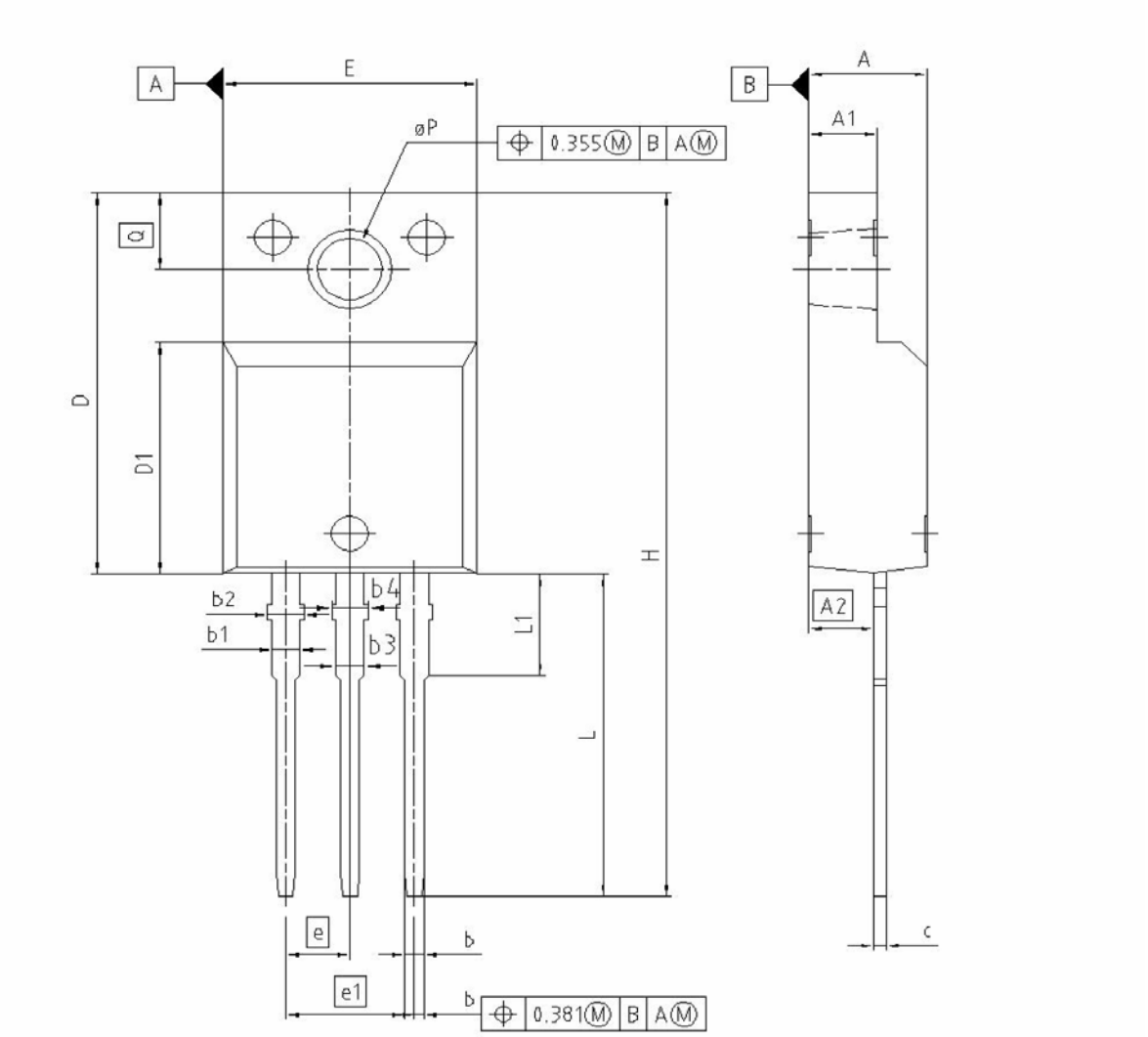
PG-TO220-3-1, PG-TO220-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO.	Z8B00003318
SCALE	0 2.5 0 2.5 5mm
EUROPEAN PROJECTION	
ISSUE DATE	23-08-2007
REVISION	05

PG-TO220-3-31 (FullPAK)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

REFERENCE
./..
SCALE 0 2.5 0 2.5 5mm
EUROPEAN PROJECTION
ISSUE DATE 08-01-2007
FILE TO220_2

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Information

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Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.
Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

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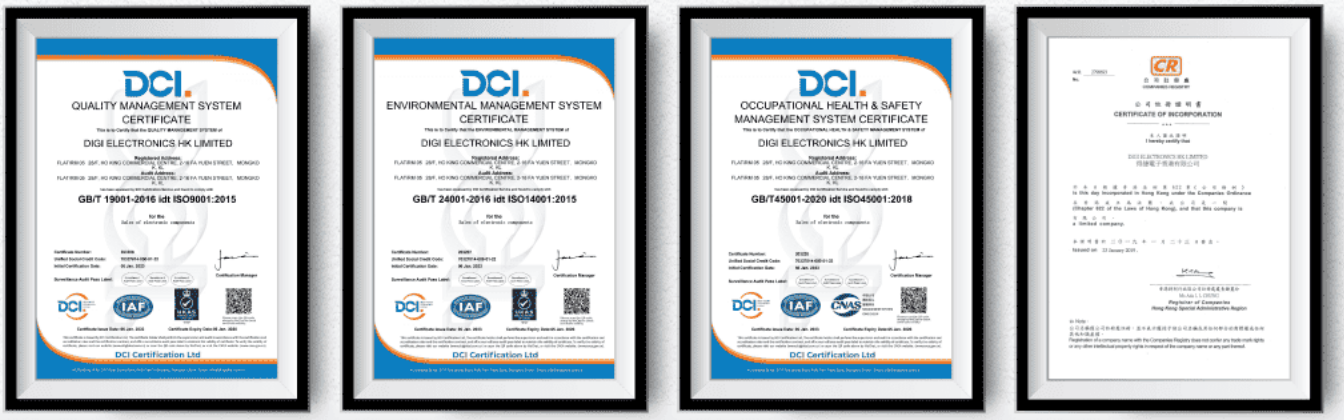

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